



#5 IDS
7/5/6

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET 033035 M 0342	SERIAL NO. 10/691,569
	APPLICANT: Kensaku MOTOKI, et al.	
	FILING DATE October 24, 2003	GROUP ART UNIT 2814

U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

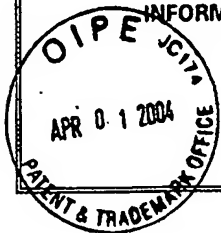
*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO	
MDP	AL	97/11518	3/27/1997	WO				
MDP	AM	07-273048	10/20/1995	JAPAN			abstract	
MDP	AN	11-135770	5/21/1999	JAPAN			abstract	
	AO							
	AP							

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

MDP	AQ	H. Okumura, et al., "Epitaxial growth of cubic and hexagonal GaN on GaAs by gas-source molecular-beam epitaxy", Appl. Phys. Lett. 59(9), August 26, 1991, pages 1058-1060, November 2002
MDP	AR	K. Naniwae, et al., "Growth of Single Crystal GaN Substrate Using Hydride Vapor Phase Epitaxy", Journal of Crystal Growth 99, 1990, pages 381-384
MDP	AS	Notice of Rejection from JPO
EXAMINER: 		DATE CONSIDERED: 9/12/2006
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		

#485
4/1/4

FORM PTO-1449	ATTY. DOCKET 33035M0342	SERIAL NO. 10/691,569
INFORMATION DISCLOSURE STATEMENT		
Applicant Kensaku Motoki, et al.		
FILING DATE October 24, 2003		GROUP ART UNIT 2814



U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
MSP	AA	5,970,314	10/19/99	Okahisa, et al.			
MSP	AB	5,962,875	10/5/99	Motoki, et al.			
MSP	AC	5,834,325	11/10/98	Motoki, et al.			

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO	
MSP	AD	WO 96/41906	12/27/96	PCT				
MSP	AE	EP 0 801 156	10/15/97	EPO				
MSP	AF	EP 0 810 674	12/3/97	EPO				

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

MSP	AG	Masaki Nagahara, et al., "Selective Growth of Cubic GaN in Small Areas on Patterned GaAs (100) Substrates by Metalorganic Vapor Phase Epitaxy", Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Vol. 33, No. 1B, Part 1, (1994), pp. 694-697, XP000596419
MSP	AH	X. Li, et al., "Characteristics of GaN Stripes Grown by Selective-Area Metalorganic Chemical Vapor Deposition", Journal of Electronic Materials, Vol. 26, No. 3, (1996), pp. 306-310, XP009004611
MSP	AI	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Matsushima H. et al., "Sub-micron fine structure of GaN by metalorganic vapor phase epitaxy (MOVPE) selective area growth (SAG) and buried structure by epitaxial lateral overgrowth (ELO)", Database accession no. 6037425 XP-002268861
MSP	AJ	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Shibata T et al., "Hybride vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth", Database accession no. 6037423 XP-002268862
MSP	AK	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Sasaoka C et al., "High-quality InGa _N MQW on low-dislocation-density GaN substrate grown by hydride vapor-phase epitaxy", Database accession no. 6037422 XP-002268863

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#3705
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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO. 33035M0342	SERIAL NO. To Be Assigned 10/691,569
	APPLICANTS: Kensaku Motoki, et al.	
	FILING DATE Herewith	GROUP ART UNIT To Be Assigned

U.S. Patent Documents

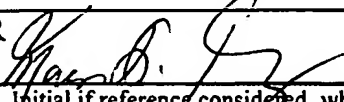
Examiner Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
MJP	AA	4,727,047	2/1988	Bozler, et al.			
	AB	6,225,650	5/2001	Tadatomo et al.			
	AC	5,843,227	12/1998	Kimura et al.			
	AD	5,846,609	12/1998	Shiralagi			
	AE	6,087,681	7/2000	Shakuda			
	AF	6,096,130	8/2000	Kimura			
	AG	6,156,581	12/2000	Vaudo et al.			

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*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
MJP	AD	09-194299	7/29/97	Japan			Abstract	
	AE	8-116090	5/7/96	Japan			Abstract	
	AF	9-255496	9/30/97	Japan			Abstract	
	AG	7-273048	10/20/95	Japan			Abstract	
	AH	51-50899	5/4/76	Japan			X	
	AI	10-265297	10/6/98	Japan			Abstract	
	AJ	10-312971	11/24/98	Japan			Abstract	
	AK	10-326751	12/8/98	Japan			Abstract	
	AL	10-321529	12/4/98	Japan			X	
	AM	09-255496	9/30/97	Japan			Abstract	

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER 	DATE CONSIDERED 9/12/2006
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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO. 33035M0342	SERIAL NO. 10 To Be Assigned 691, 569
	APPLICANTS: Kensaku Motoki, et al.	
	FILING DATE Herewith	GROUP ART UNIT To Be Assigned

U.S. Patent Documents

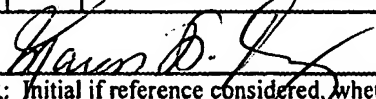
Examiner Initials	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
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	AB					

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	AC						
	AD						

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

	AE	Chinese Office Action mailed June 20, 2003.
MSF	AF	U. Akira et al. "Thick GaN Epitaxial Growth With Low Dislocation Density by Hydride Vapor Phase Epitaxy" Japanese Journal of Applied Physics, 15 July 1997, Part. 2, Vol. 36, No. 7B, pp. L899-L902.
	AG	S. Akira et al. "Defect Structure in Selectively Grown GaN Films With Low Threading Dislocation Density" Applied Physics Letters, 20 October 1997, Vol. 71, No. 16, pp. 2259-2261.
	AH	H. Shima et al. "Selective Growth of GaN on Submicron Pattern by MOVPE (in Japanese)" Technical Report of IEICE, Vol. 97, No. 61, 23 May 1997 (Tokyo), pp. 41-46.
	AI	T. Shibata et al. "Preparation of High-Quality GaN Bulk Single Crystal by Selective HVPE Growth (in Japanese)", Technical Report of IEICE, Vol. 97, No. 61, 23 May 1997 (Tokyo), pp. 35-40.
	AJ	K. Shota et al. "Fabrication of GaN Hexagonal Pyramids on Dot-Patterned GaN/Sapphire Substrates Via Selective Metalorganic Vapor Phase Epitaxy" Japanese Journal of Applied Physics, 15 September 1995, Part 2, Vol. 34, No. 9B, pp. L1184-L1186.
	AK	International Preliminary Examination Report (PCT/IPEA/409) (translated) for J PCT/JP98/04908.
	AL	International Search Report for PCT/JP98/04908.
	AM	Cover page of WO99/23693.
	AN	Forms PCT/IB/304 and PCT/IB/308.
MSF	AO	Korean Office Action mailed April 23, 2003

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